



520.37546X00

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#19/C  
11/20/02  
Smith

Applicants: TORII et al.  
Serial No.: 09/391,250  
Filed: September 7, 1999  
For: MEMORY STRUCTURE WITH A FERROELECTRIC  
CAPACITOR AND A FABRICATION METHOD  
THEREOF  
(As amended)  
Group: 2811  
Examiner: C. Nguyen

RECEIVED  
NOV 15 2002  
TECHNOLOGY CENTER 2800**AMENDMENT-SUBMISSION WITH RCE**

Assistant Commissioner  
for Patents  
Washington, D.C. 20231

November 12, 2002

Sir:

In accordance with the provisions of 37 C.F.R. 1.114, permitting submission of an Amendment with the filing of a RCE, applicants hereby respectfully request entry of the following amendment, noting that a Petition for Extension of Time is being filed herewith for extending the time for filing of the RCE with the present amendment:

**IN THE CLAIMS:**

Please amend claims 1, 7 and 14 as follows:

1. (Amended) A semiconductor device comprising:
- an insulating film formed on a substrate provided with a transistor and having an opening portion;
  - a conductive film formed in the opening portion; and

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